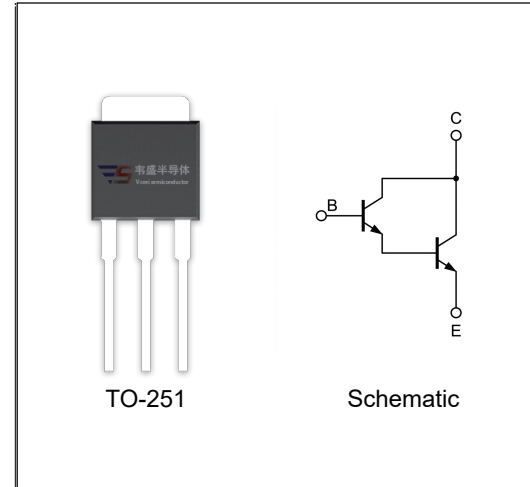


MJD127 TRANSISTOR (PNP)

FEATURES

- High DC Current Gain
- Electrically Similar to Popular TIP127
- Built-in a Damper Diode at E-C



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-100	V
V _{CEO}	Collector-Emitter Voltage	-100	V
V _{EB0}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-8	A
I _{CM}	Peak Collector Current(tp<1ms)	-16	A
P _C	Collector Power Dissipation	1.5	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1mA, I_E = 0$	-100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -30mA, I_B = 0$	-100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10mA, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -100V, I_E = 0$			-10	μA
Collector-emitter cut-off current	I_{CEO}	$V_{CE} = -50V, I_B = 0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-2	mA
DC current gain	$h_{FE(1)}$	$V_{CE} = -4V, I_C = -4A$	1000		12000	
	$h_{FE(2)}$	$V_{CE} = -4V, I_C = -8A$	100			
Collector-emitter saturation voltage	$V_{CE(sat)1}^*$	$I_C = -4A, I_B = -16mA$			-2	V
	$V_{CE(sat)2}^*$	$I_C = -8A, I_B = -80mA$			-4	V
Base-emitter saturation voltage	$V_{BE(sat)}^*$	$I_C = -8A, I_B = -80mA$			-4.5	V
Base-emitter voltage	V_{BE}^*	$V_{CE} = -4V, I_C = -4A$			-2.8	V
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 0.1MHz$			300	pF

*Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

